

NTMFS4936N, NTMFS4936NC

MOSFET – Power, Single, N-Channel, SO-8 FL 30 V, 79 A



ON Semiconductor®

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Features

- Low $R_{DS(on)}$, Low Capacitance and Optimized Gate Charge to Minimize Conduction, Driver and Switching Losses
- Next Generation Enhanced Body Diode, Engineered for Soft Recovery, Provides Schottky-Like Performance
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

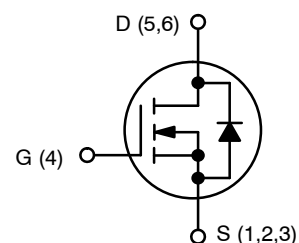
Applications

- CPU Power Delivery
- DC-DC Converters

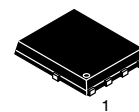
MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise stated)

Parameter	Symbol	Value	Unit	
Drain-to-Source Voltage	V_{DSS}	30	V	
Gate-to-Source Voltage	V_{GS}	± 20	V	
Continuous Drain Current $R_{\theta JA}$ (Note 1)	I_D	$T_A = 25^\circ\text{C}$	19.5	A
		$T_A = 100^\circ\text{C}$	12.3	
Power Dissipation $R_{\theta JA}$ (Note 1)	P_D	2.62	W	
Continuous Drain Current $R_{\theta JA} \leq 10$ s (Note 1)	I_D	$T_A = 25^\circ\text{C}$	35	A
		$T_A = 100^\circ\text{C}$	22	
Power Dissipation $R_{\theta JA} \leq 10$ s (Note 1)	P_D	8.4	W	
Continuous Drain Current $R_{\theta JA}$ (Note 2)	I_D	$T_A = 25^\circ\text{C}$	11.6	A
		$T_A = 100^\circ\text{C}$	7.3	
Power Dissipation $R_{\theta JA}$ (Note 2)	P_D	0.92	W	
Continuous Drain Current $R_{\theta JC}$ (Note 1)	I_D	$T_C = 25^\circ\text{C}$	79	A
		$T_C = 100^\circ\text{C}$	50	
Power Dissipation $R_{\theta JC}$ (Note 1)	P_D	43	W	
Pulsed Drain Current	$T_A = 25^\circ\text{C}, t_p = 10 \mu\text{s}$	I_{DM}	235	A
Current Limited by Package	$T_A = 25^\circ\text{C}$	I_{Dmax}	100	A
Operating Junction and Storage Temperature	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$	
Source Current (Body Diode)	I_S	39.2	A	
Drain to Source DV/DT	dV/dt	6.0	V/ns	

$V_{(BR)DSS}$	$R_{DS(ON)}$ MAX	I_D MAX
30 V	3.8 m Ω @ 10 V	79 A
	4.8 m Ω @ 4.5 V	

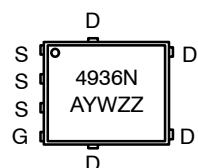


N-CHANNEL MOSFET



SO-8 FLAT LEAD
CASE 488AA
STYLE 1

MARKING DIAGRAM



4936N = Specific Device Code
A = Assembly Location
Y = Year
W = Work Week
ZZ = Lot Traceability

ORDERING INFORMATION

Device	Package	Shipping†
NTMFS4936NT1G	SO-8 FL (Pb-Free)	1500 / Tape & Reel
NTMFS4936NT3G	SO-8 FL (Pb-Free)	5000 / Tape & Reel
NTMFS4936NCT1G	SO-8 FL (Pb-Free)	1500 / Tape & Reel
NTMFS4936NCT3G	SO-8 FL (Pb-Free)	5000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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MAXIMUM RATINGS (T_J = 25°C unless otherwise stated)

Parameter	Symbol	Value	Unit
Single Pulse Drain-to-Source Avalanche Energy (T _J = 25°C, V _{DD} = 50 V, V _{GS} = 10 V, I _L = 44 A _{pk} , L = 0.1 mH, R _G = 25 Ω)	E _{AS}	96.8	mJ
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)	T _L	260	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

- Surface-mounted on FR4 board using 1 sq-in pad, 1 oz Cu.
- Surface-mounted on FR4 board using the minimum recommended pad size.

THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Junction-to-Case (Drain)	R _{θJC}	2.9	°C/W
Junction-to-Ambient – Steady State (Note 3)	R _{θJA}	47.7	
Junction-to-Ambient – Steady State (Note 4)	R _{θJA}	135.2	
Junction-to-Ambient – (t ≤ 10 s) (Note 3)	R _{θJA}	14.8	

- Surface-mounted on FR4 board using 1 sq-in pad, 1 oz Cu.
- Surface-mounted on FR4 board using the minimum recommended pad size.

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0 V, I _D = 250 μA	30			V
Drain-to-Source Breakdown Voltage (transient)	V _{(BR)DSS(t)}	V _{GS} = 0 V, I _{D(aval)} = 18.5 A, T _{case} = 25°C, t _{transient} = 100 ns	34			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	V _{(BR)DSS} /T _J			15		mV/°C
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V, V _{DS} = 24 V	T _J = 25°C		1.0	μA
			T _J = 125°C		10	
Gate-to-Source Leakage Current	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±20 V			±100	nA

ON CHARACTERISTICS (Note 5)

Gate Threshold Voltage	V _{GS(TH)}	V _{GS} = V _{DS} , I _D = 250 μA	1.2	1.6	2.2	V	
Negative Threshold Temperature Coefficient	V _{GS(TH)} /T _J			4.0		mV/°C	
Drain-to-Source On Resistance	R _{DS(on)}	V _{GS} = 10 V	I _D = 30 A		2.9	3.8	mΩ
			I _D = 15 A		2.9		
		V _{GS} = 4.5 V	I _D = 30 A		3.9	4.8	
			I _D = 15 A		3.9		
Forward Transconductance	g _{FS}	V _{DS} = 1.5 V, I _D = 15 A		50		S	

CHARGES, CAPACITANCES & GATE RESISTANCE

Input Capacitance	C _{ISS}	V _{GS} = 0 V, f = 1 MHz, V _{DS} = 15 V		3044		pF
Output Capacitance	C _{OSS}			1014		
Reverse Transfer Capacitance	C _{RSS}			39		
Capacitance Ratio	C _{RSS} /C _{ISS}	V _{GS} = 0 V, V _{DS} = 15 V, f = 1 MHz		0.013	0.026	

- Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%.
- Switching characteristics are independent of operating junction temperatures.

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ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
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CHARGES, CAPACITANCES & GATE RESISTANCE

Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 4.5\text{ V}, V_{DS} = 15\text{ V}; I_D = 30\text{ A}$		19		nC
Threshold Gate Charge	$Q_{G(TH)}$			4.6		
Gate-to-Source Charge	Q_{GS}			9.2		
Gate-to-Drain Charge	Q_{GD}			2.4		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 10\text{ V}, V_{DS} = 15\text{ V}; I_D = 30\text{ A}$		43		nC

SWITCHING CHARACTERISTICS (Note 6)

Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = 4.5\text{ V}, V_{DS} = 15\text{ V}, I_D = 15\text{ A}, R_G = 3.0\ \Omega$		15.5		ns
Rise Time	t_r			20.6		
Turn-Off Delay Time	$t_{d(OFF)}$			24.6		
Fall Time	t_f			7.0		
Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = 10\text{ V}, V_{DS} = 15\text{ V}, I_D = 15\text{ A}, R_G = 3.0\ \Omega$		10.4		ns
Rise Time	t_r			19		
Turn-Off Delay Time	$t_{d(OFF)}$			29		
Fall Time	t_f			8.0		

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V_{SD}	$V_{GS} = 0\text{ V}, I_S = 30\text{ A}$	$T_J = 25^\circ\text{C}$		0.8	1.1	V
			$T_J = 125^\circ\text{C}$		0.65		
Reverse Recovery Time	t_{RR}	$V_{GS} = 0\text{ V}, dI_S/dt = 100\text{ A}/\mu\text{s}, I_S = 30\text{ A}$			39		ns
Charge Time	t_a				21.5		
Discharge Time	t_b				17.5		
Reverse Recovery Charge	Q_{RR}				36		

PACKAGE PARASITIC VALUES

Source Inductance	L_S	$T_A = 25^\circ\text{C}$		0.65		nH
Drain Inductance	L_D			0.005		nH
Gate Inductance	L_G			1.84		nH
Gate Resistance	R_G			1.1	2.0	Ω

5. Pulse Test: pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$.
 6. Switching characteristics are independent of operating junction temperatures.

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TYPICAL CHARACTERISTICS

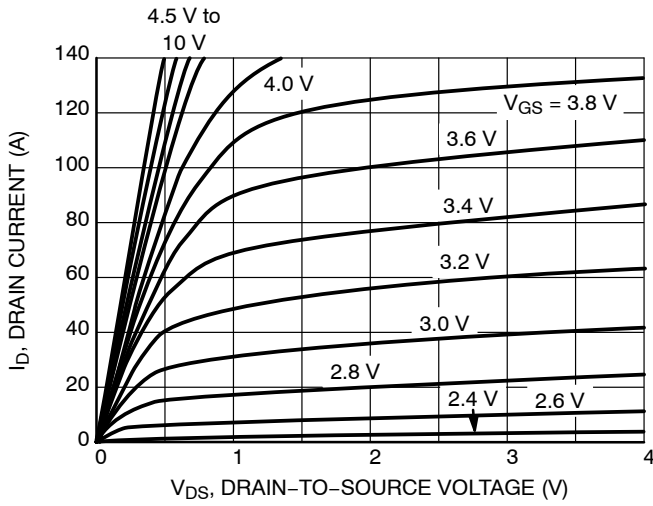


Figure 1. On-Region Characteristics

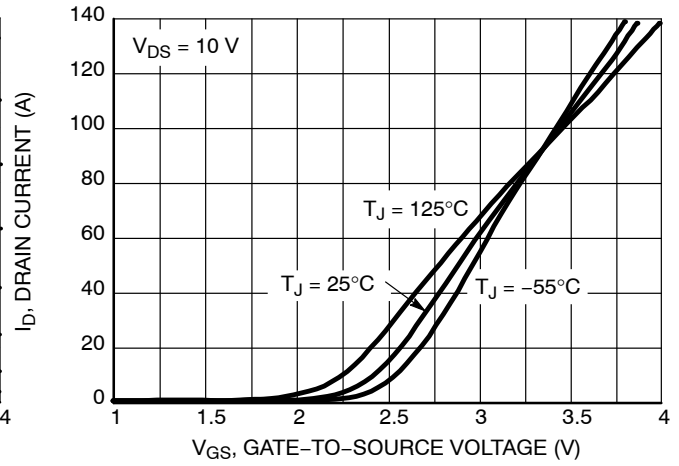


Figure 2. Transfer Characteristics

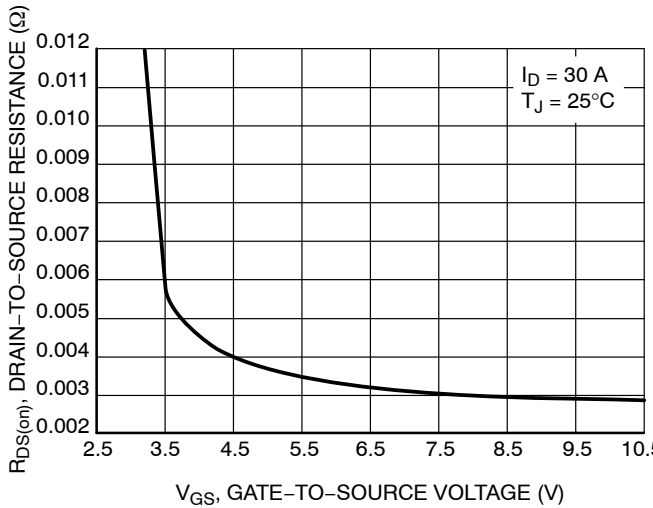


Figure 3. On-Resistance vs. Gate-to-Source Voltage

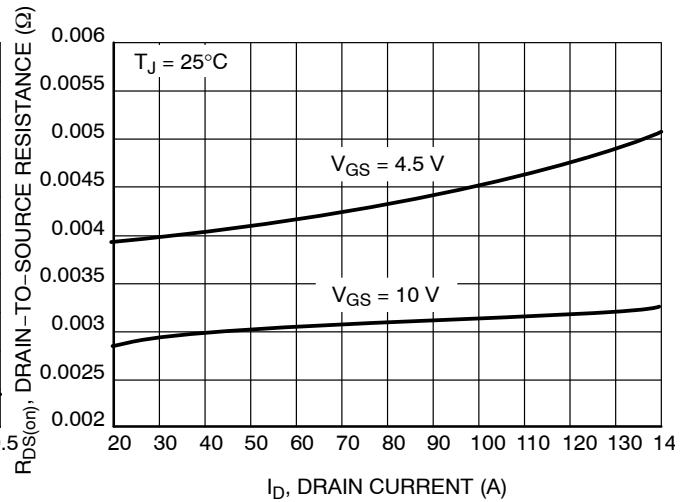


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

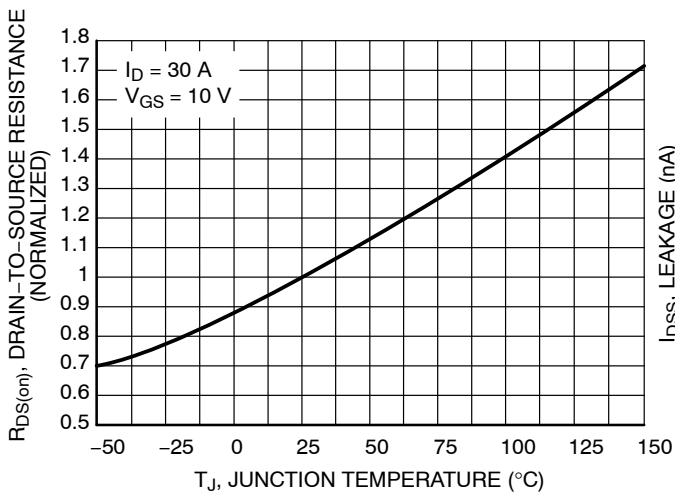


Figure 5. On-Resistance Variation with Temperature

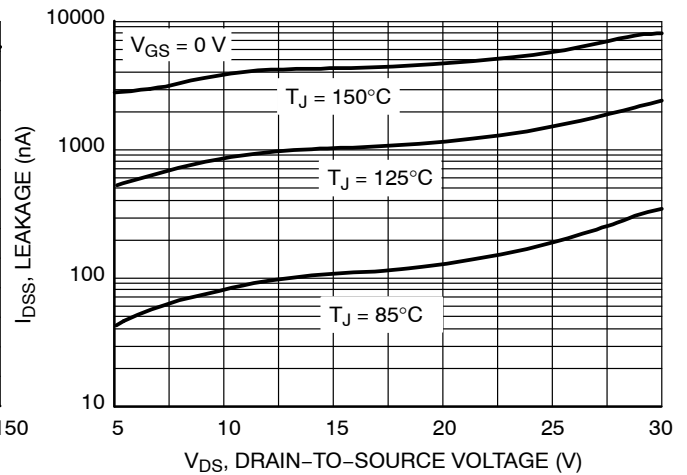


Figure 6. Drain-to-Source Leakage Current vs. Voltage

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TYPICAL CHARACTERISTICS

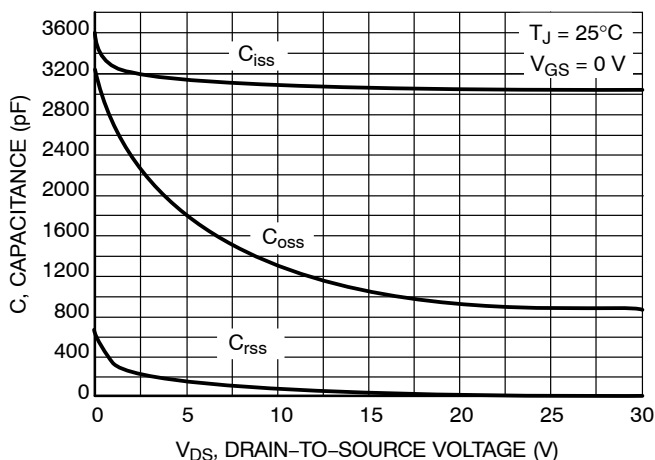


Figure 7. Capacitance Variation

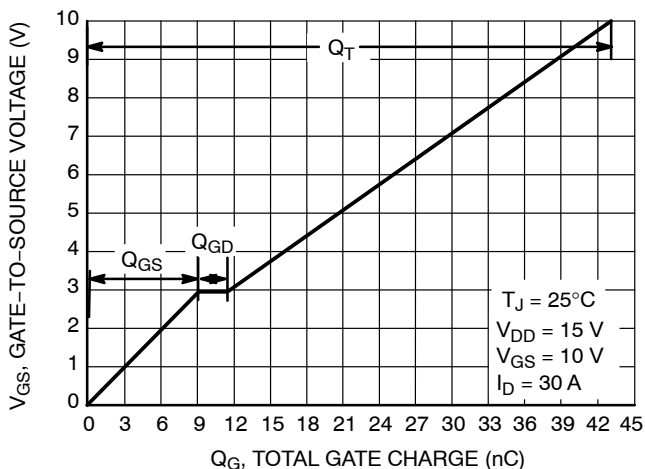


Figure 8. Gate-To-Source and Drain-To-Source Voltage vs. Total Charge

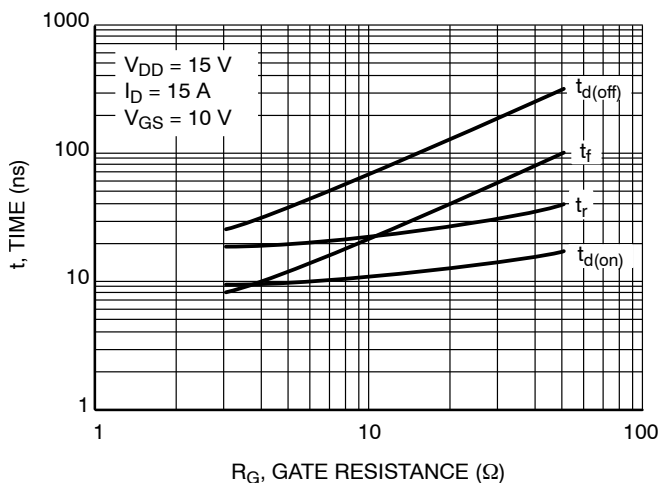


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

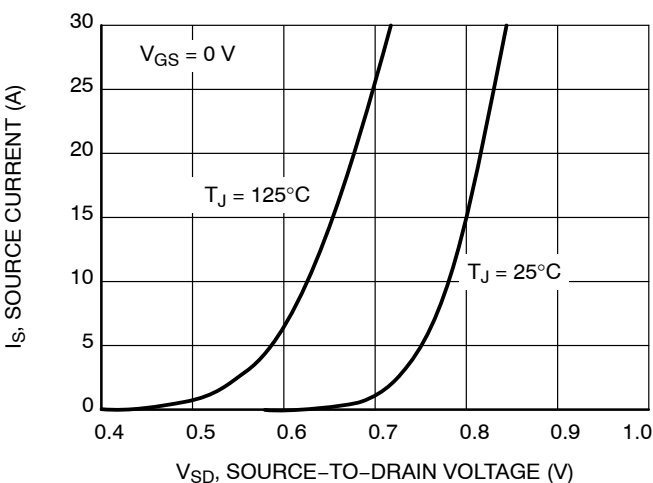


Figure 10. Diode Forward Voltage vs. Current

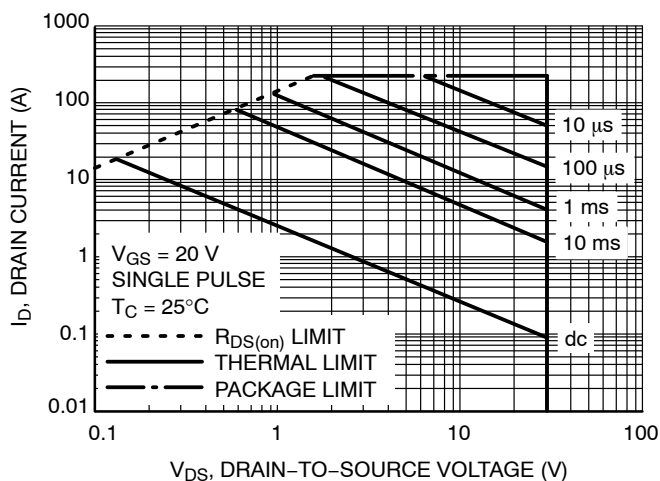


Figure 11. Maximum Rated Forward Biased Safe Operating Area

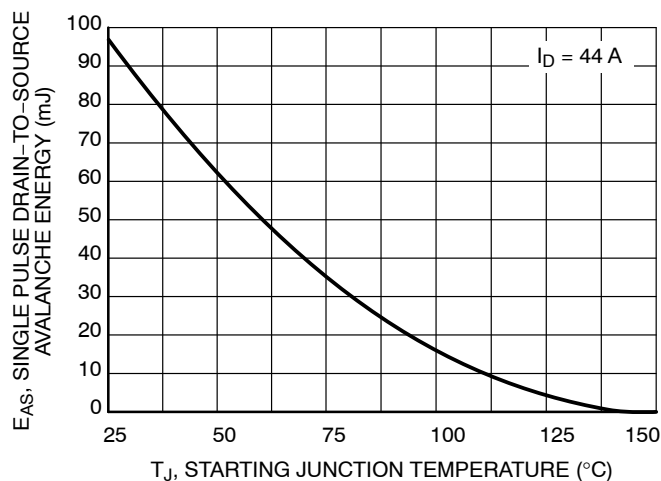


Figure 12. Maximum Avalanche Energy vs. Starting Junction Temperature

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TYPICAL CHARACTERISTICS

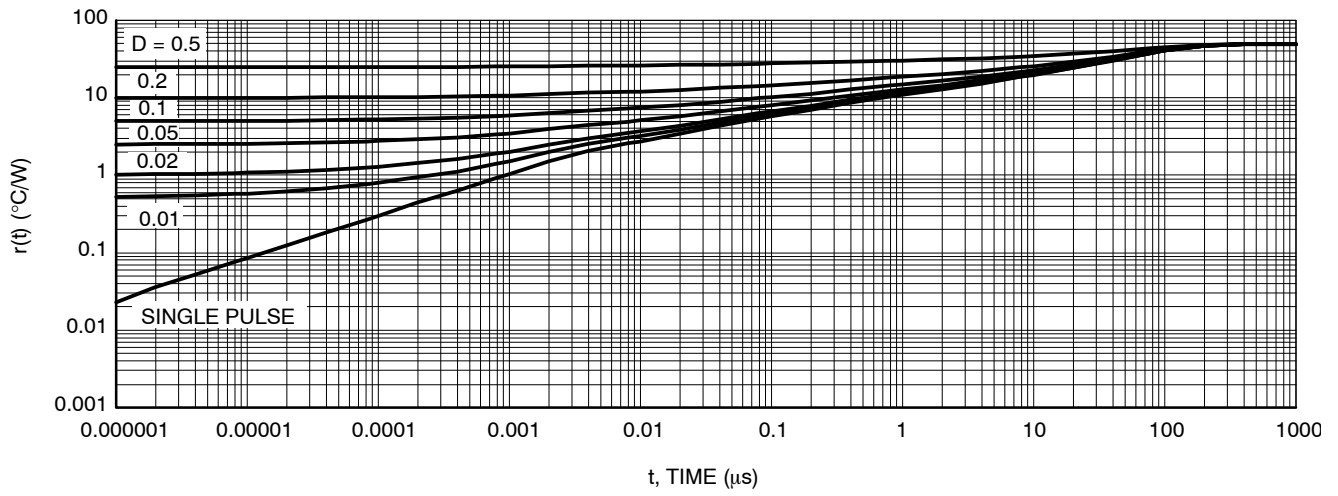


Figure 13. Thermal Response

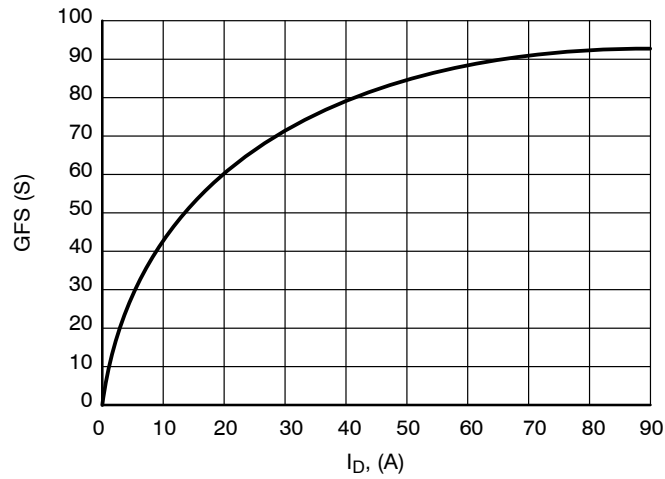


Figure 14. GFS vs. I_D

MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS



1
SCALE 2:1

DFN5 5x6, 1.27P
(SO-8FL)
CASE 488AA
ISSUE N

DATE 25 JUN 2018



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION D1 AND E1 DO NOT INCLUDE MOLD FLASH PROTRUSIONS OR GATE BURRS.

DIM	MILLIMETERS		
	MIN	NOM	MAX
A	0.90	1.00	1.10
A1	0.00	---	0.05
b	0.33	0.41	0.51
c	0.23	0.28	0.33
D	5.00	5.15	5.30
D1	4.70	4.90	5.10
D2	3.80	4.00	4.20
E	6.00	6.15	6.30
E1	5.70	5.90	6.10
E2	3.45	3.65	3.85
e	1.27 BSC		
G	0.51	0.575	0.71
K	1.20	1.35	1.50
L	0.51	0.575	0.71
L1	0.125 REF		
M	3.00	3.40	3.80
θ	0°	---	12°

GENERIC MARKING DIAGRAM*



- XXXXXX = Specific Device Code
- A = Assembly Location
- Y = Year
- W = Work Week
- ZZ = Lot Traceability

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.



- STYLE 1:
PIN 1. SOURCE
2. SOURCE
3. SOURCE
4. GATE
5. DRAIN
- STYLE 2:
PIN 1. ANODE
2. ANODE
3. ANODE
4. NO CONNECT
5. CATHODE

DIMENSIONS: MILLIMETERS

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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